

Si9936DY*

Dual N-Channel Enhancement Mode MOSFET

General Description

These N-Channel Enhancement Mode MOSFETs are produced using Fairchild Semiconductor's advance process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

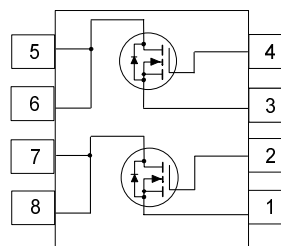
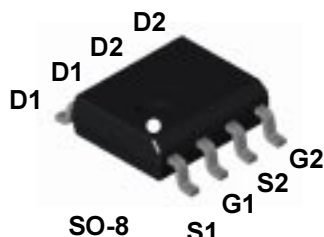
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- 5.0 A, 30 V. $R_{DS(ON)} = 0.050 \Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 0.080 \Omega @ V_{GS} = 4.5 \text{ V}$
- Low gate charge.
- Fast switching speed.
- High power and current handling capability.

Applications

- Battery switch
- Load switch
- Motor controls



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (Note 1a) - Pulsed	5.0	A
		40	
P _D	Power Dissipation for Single Operation	2.0	W
	Power Dissipation for Single Operation (Note 1a)	1.6	
	(Note 1b)	1	
	(Note 1c)	0.9	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	40	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
9936	SI9936DY	13"	12mm	2500 units

* Die and manufacturing source subject to change without prior notification.

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		70		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			2 20	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1			V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-4.5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_D = 3.9\text{ A}$		0.044 0.066 0.066	0.050 0.100 0.080	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	40			A
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 5\text{ A}$		8		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		525		pF
C_{oss}	Output Capacitance			315		pF
C_{rss}	Reverse Transfer Capacitance			185		pF

Switching Characteristics (Note 2)

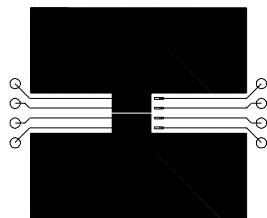
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A}, R_L = 15\ \Omega$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		12	30	ns
t_r	Turn-On Rise Time			10	25	ns
$t_{d(off)}$	Turn-Off Delay Time			25	50	ns
t_f	Turn-Off Fall Time			10	50	ns
t_{rr}	Drain-Source Reverse Recovery Time	$I_F = 5\text{ A}, di/dt = 100\text{A}/\mu\text{s}$			160	nS
Q_g	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 5\text{ A},$ $V_{GS} = 10\text{ V}$		17	35	nC
Q_{gs}	Gate-Source Charge			1.5		nC
Q_{gd}	Gate-Drain Charge			3.7		nC

Drain-Source Diode Characteristics and Maximum Ratings

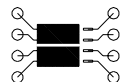
I_S	Maximum Continuous Drain-Source Diode Forward Current			1.7	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.7\text{ A}$ (Note 2)		0.78	1.2	V

Notes:

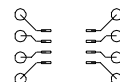
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in^2 pad of 2 oz. copper.



b) 125°C/W when mounted on a 0.02 in^2 pad of 2 oz. copper.



c) 135°C/W when mounted on a 0.003 in^2 pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

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